IN THE CLAIMS:

Please amend the claims as follows:

Claims 1-8 (cancelled)

9. (currently amended) A heat treating method for a silicon single crystal wafer related to a perfect crystal produced by a Czochralski method, ~~characterized in~~comprising the steps of ~~that~~ maintaining a heat treatment temperature at the initial entry of the silicon single crystal wafer to be a target of the heat treatment ~~is~~ at less than 500°C ~~or less~~, and maintaining a temperature ramping rate in a temperature range from the heat treatment temperature at initial entry to ~~an ultimate~~a maximum temperature ~~set~~ in a range of 700°C - 900°C, ~~is set to~~said ramping rate being 1°C/min or less.

10. (currently amended) A heat treating method for a silicon single crystal wafer related to a perfect crystal produced by a Czochralski method, ~~characterized in~~comprising the steps of ~~that~~ maintaining a heat treatment temperature at the initial entry of the silicon single crystal wafer to be a target of the heat treatment ~~is~~ at less than 500°C ~~or less~~, and maintaining a temperature ramping rate in a temperature range from the heat treatment temperature at initial entry to ~~an ultimate~~a maximum temperature ~~set~~ in a range of 700°C - 900°C, said ramping rate being ~~is set to~~ 1°C/min or less, so as to make uniform the distribution of an oxide precipitate density of the silicon single crystal wafer after heat treatment.

11. (currently amended) A heat treating method for a silicon single crystal wafer related to a perfect crystal produced by a Czochralski method, comprising the steps of ~~characterized in~~ ~~that~~ ~~a~~controlling heat treatment temperature at the initial entry of the silicon single crystal wafer to be a target of the heat treatment and controlling a temperature ramping rate from the heat treatment

temperature at initial entry to ~~an ultimate~~a maximum temperature ~~set~~ maintaining in a range of 700°C - 900°C ~~are adjusted~~ so as to adjust the distribution of an oxide precipitate density of the silicon single crystal wafer after heat treatment.

12. (original) The method according to Claim 9, ~~characterized in that~~wherein the oxygen concentration of the perfect crystal is 13×10^{17} atoms/cm^3 or less.

13. (currently amended) A silicon single crystal wafer produced by the method according to Claim 12.

Claims 14-23 (cancelled)